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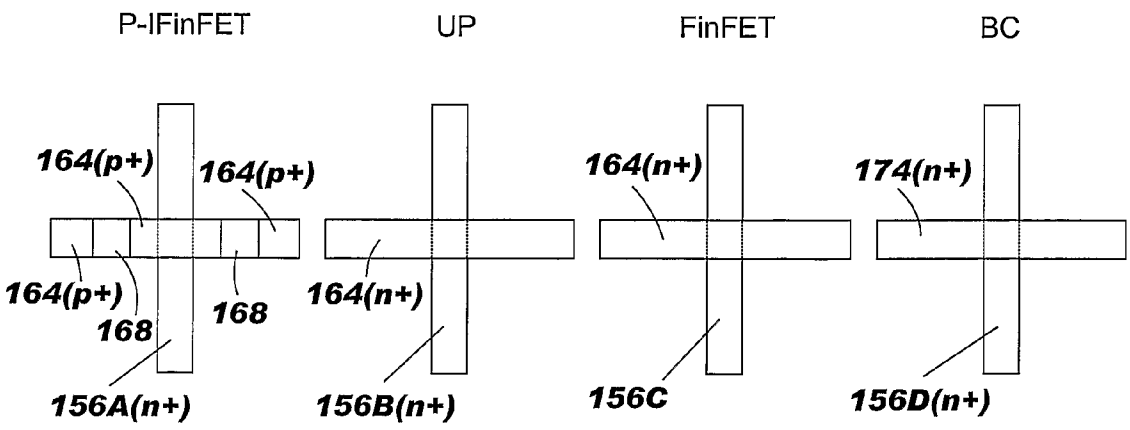
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(54) Title: FINFET SRAM CELL USING INVERTED FINFET THIN FILM TRANSISTORS



(57) Abstract: An integrated circuit, such as a SRAM cell (130), including an inverted FinFET transistor (P2) and a FinFET transistor (N3). The inverted FinFET transistor includes a first gate region (108) formed by semiconductor structure (100) on a substrate, a first body region comprised of a semiconductor layer (104), having a first channel region (112) disposed on the first gate region and a source (110) and drain (114) formed on either side of the first channel region. The FinFET transistor (N3) is coupled to the inverted FinFET transistor, and includes a second body region formed by the semiconductor structure (102), having a second channel region (118) and a source (116) and drain (120) formed on either side of the second channel region, and a second gate region (122) comprised of the semiconductor layer, disposed on the second channel region.

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